
HM5164400 Series

HM5165400 Series

64 M FP DRAM (16-Mword $\times$ 4-bit)
8 k Refresh/4 k Refresh

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ADE-203-812B (Z)
Rev. 1.0
Feb. 27, 1998

Description

The Hitachi HM5164400 Series, HM5165400 Series are 64M-bit dynamic RAMs organized as 16,777,216-word $\times$ 4-bit. They have realized high performance and low power by employing CMOS process technology. The HM5164400 Series, HM5165400 Series offer Fast Page Mode as a high speed access mode. They have the package variations of standard 32-pin plastic SOJ and standard 32-pin plastic TSOPII.

Features

- Single 3.3 V supply: 3.3 V $\pm$ 0.3 V
- Access time: 50 ns/60 ns (max)
- Power dissipation
 - Active: 396 mW/360 mW (max) (HM5164400 Series)
: 468 mW/396 mW (max) (HM5165400 Series)
 - Standby : 1.8 mW (max) (CMOS interface)
: 0.54 mW (max) (L-version)
- Fast page mode capability
- Refresh cycles
 - $\overline{\text{RAS}}$ -only refresh
 - 8192 cycles /64 ms (HM5164400)
/128 ms (HM5164400L) (L-version)
 - 4096 cycles /64 ms (HM5165400)
/128 ms (HM5165400L) (L-version)
 - CBR/Hidden refresh
 - 4096 cycles /64 ms (HM5164400, HM5165400)
/128 ms (HM5164400L, HM5165400L) (L-version)

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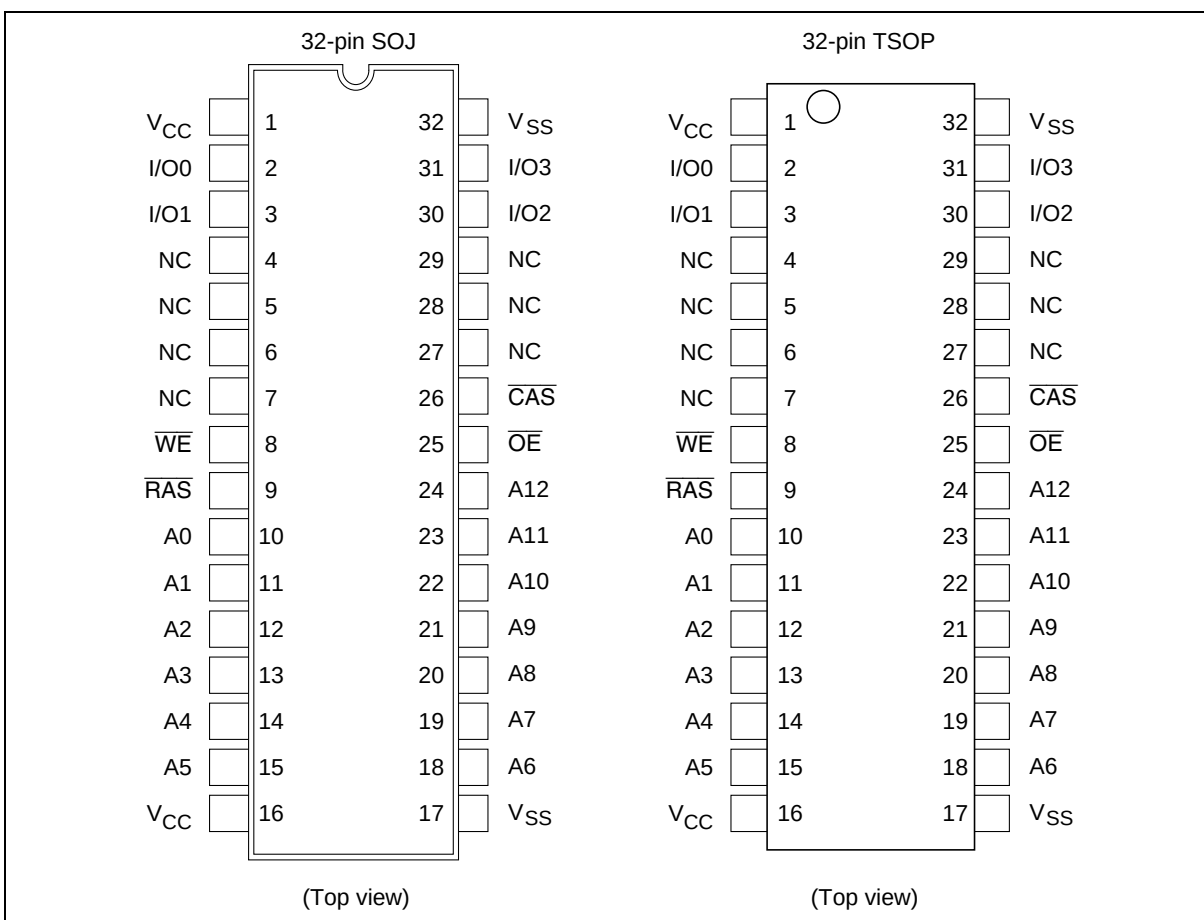
- 4 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh
 - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh
 - Hidden refresh
 - Self refresh (L-version)
- Battery backup operation (L-version)

Ordering Information

Type No.	Access time	Package
HM5164400J-5	50 ns	400-mil 32-pin plastic SOJ (CP-32DC)
HM5164400J-6	60 ns	
HM5164400LJ-5	50 ns	
HM5164400LJ-6	60 ns	
HM5165400J-5	50 ns	
HM5165400J-6	60 ns	
HM5165400LJ-5	50 ns	
HM5165400LJ-6	60 ns	
HM5164400TT-5	50 ns	400-mil 32-pin plastic TSOP II (TTP-32DC)
HM5164400TT-6	60 ns	
HM5164400LTT-5	50 ns	
HM5164400LTT-6	60 ns	
HM5165400TT-5	50 ns	
HM5165400TT-6	60 ns	
HM5165400LTT-5	50 ns	
HM5165400LTT-6	60 ns	

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Pin Arrangement (HM5164400 Series)

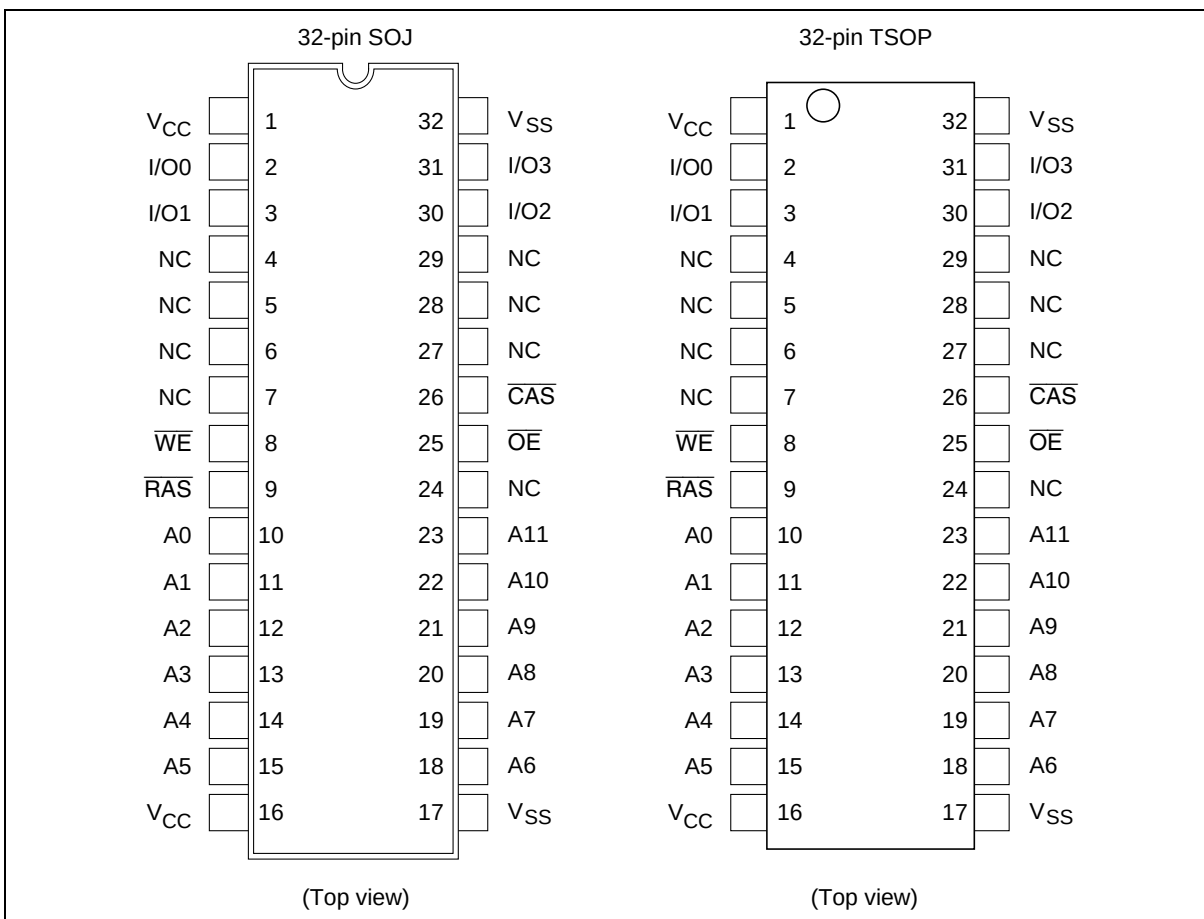


Pin Description

Pin name	Function
A0 to A12	Address input - Row/Refresh address A0 to A12 - Column address A0 to A10
I/O0 to I/O3	Data input/output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Write enable
$\overline{\text{OE}}$	Output enable
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

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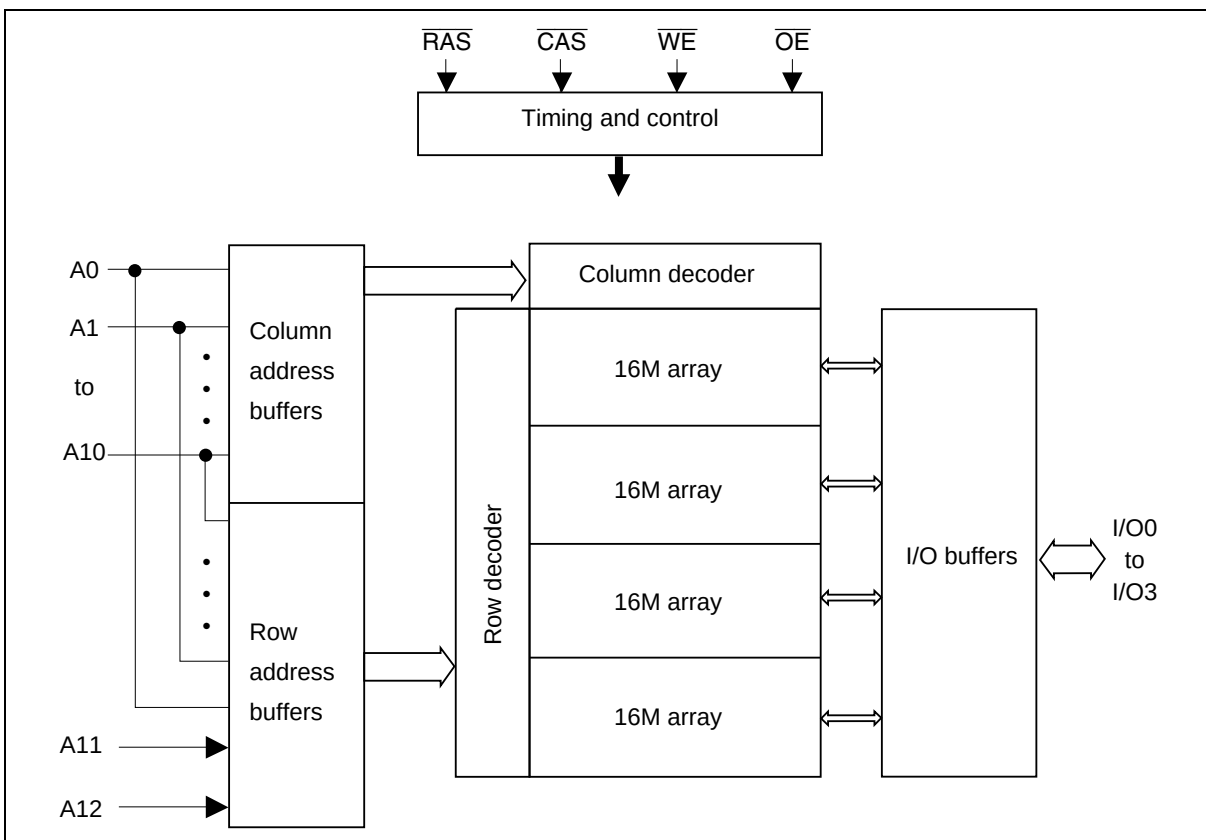
Pin Arrangement (HM5165400 Series)



Pin Description

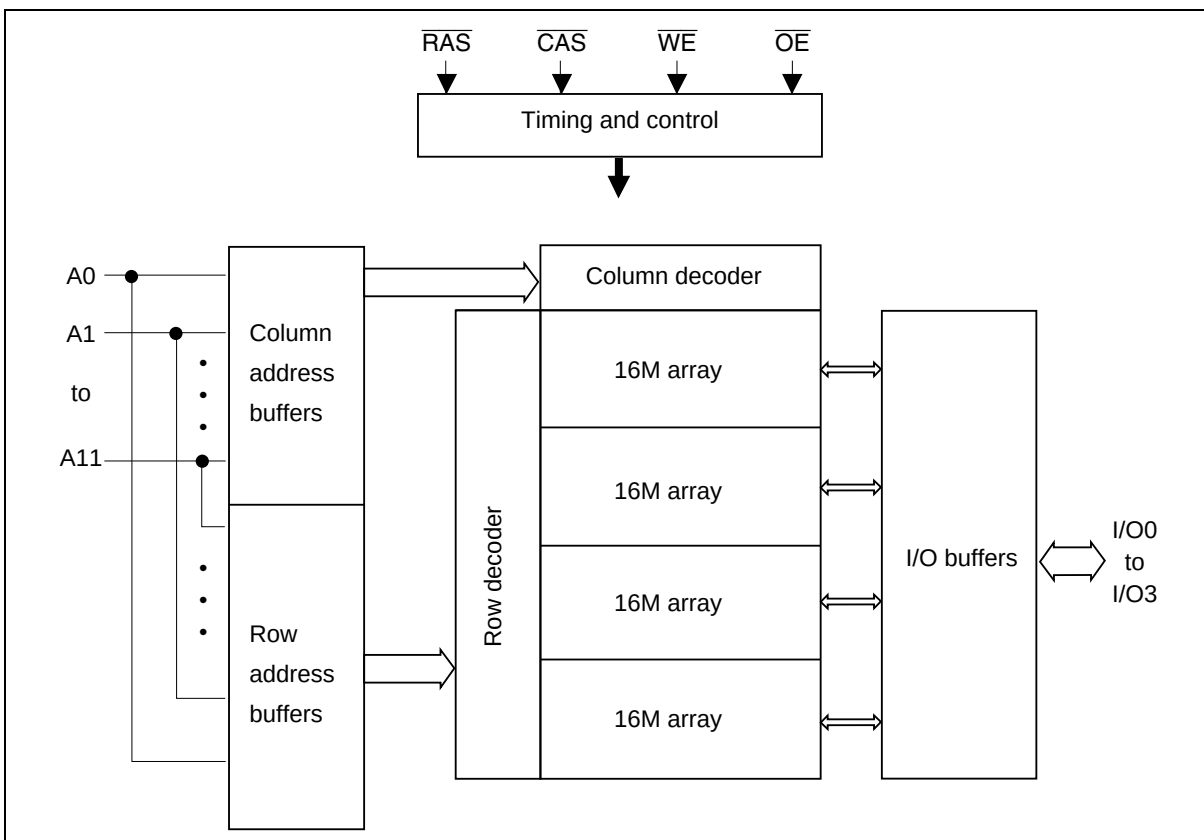
Pin name	Function
A0 to A11	Address input - Row/Refresh address A0 to A11 - Column address A0 to A11
I/O0 to I/O3	Data input/output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Write enable
$\overline{\text{OE}}$	Output enable
V _{cc}	Power supply
V _{ss}	Ground
NC	No connection

Block Diagram (HM5164400 Series)



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Block Diagram (HM5165400 Series)



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Operation Table

$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	I/O 0 to I/O 3	Operation
H	×	×	×	High-Z	Standby
L	L	H	L	Dout	Read cycle
L	L	L ^{*2}	×	Din	Early write cycle
L	L	L ^{*2}	H	Din	Delayed write cycle
L	L	H to L	L to H	Dout/Din	Read-modify-write cycle
L	H	×	×	High-Z	$\overline{\text{RAS}}$ -only refresh cycle
H to L	L	H	×	High-Z	$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle or Self refresh cycle (L-version)
L	L	H	H	High-Z	Read cycle (Output disabled)

Notes: 1. H: V_{IH} (inactive), L: V_{IL} (active), ×: V_{IH} or V_{IL}
 2. $t_{WCS} \geq 0$ ns: Early write cycle
 $t_{WCS} < 0$ ns: Delayed write cycle

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Terminal voltage on any pin relative to V_{SS}	V_T	-0.5 to $V_{CC} + 0.5$ (≤ 4.6 V (max))	V
Power supply voltage relative to V_{SS}	V_{CC}	-0.5 to $+4.6$	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	1.0	W
Storage temperature	Tstg	-55 to $+125$	°C

DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	V_{CC}	3.0	3.3	3.6	V	1, 2
	V_{SS}	0	0	0	V	2
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	1
Input low voltage	V_{IL}	-0.3	—	0.8	V	1
Ambient temperature range	T_a	0	—	70	°C	

Notes: 1. All voltage referred to V_{SS} .
 2. The supply voltage with all V_{CC} pins must be on the same level. The supply voltage with all V_{SS} pins must be on the same level.

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DC Characteristics (HM5164400 Series)

		HM5164400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Test conditions
Operating current* ¹ , * ²	I _{CC1}	—	110	—	100	mA	t _{RC} = min
Standby current	I _{CC2}	—	2	—	2	mA	TTL interface RAS, CAS = V _{IH} Dout = High-Z
		—	0.5	—	0.5	mA	CMOS interface RAS, CAS ≥ V _{CC} − 0.2 V Dout = High-Z
Standby current (L-version)	I _{CC2}	—	150	—	150	μA	CMOS interface RAS, CAS ≥ V _{CC} − 0.2 V Dout = High-Z
RAS-only refresh current* ²	I _{CC3}	—	110	—	100	mA	t _{RC} = min
Standby current* ¹	I _{CC5}	—	5	—	5	mA	RAS = V _{IH} , CAS = V _{IL} Dout = enable
CAS-before-RAS refresh current	I _{CC6}	—	110	—	100	mA	t _{RC} = min
Fast page mode current* ¹ , * ³	I _{CC7}	—	90	—	80	mA	RAS = V _{IL} , CAS cycle, t _{PC} = t _{PC} min
Battery backup current* ⁴ (Standby with CBR refresh) (L-version)	I _{CC10}	—	500	—	500	μA	CMOS interface Dout = High-Z CBR refresh: t _{RC} = 31.3 μs t _{RAS} ≤ 0.3 μs
Self refresh mode current (L-version)	I _{CC11}	—	400	—	400	μA	CMOS interface RAS, CAS ≤ 0.2 V Dout = High-Z
Input leakage current	I _{LI}	−5	5	−5	5	μA	0 V ≤ Vin ≤ V _{CC} + 0.3 V
Output leakage current	I _{LO}	−5	5	−5	5	μA	0 V ≤ Vout ≤ V _{CC} Dout = disable
Output high voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = −2 mA
Output low voltage	V _{OL}	0	0.4	0	0.4	V	Low Iout = 2 mA

- Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.
2. Address can be changed once or less while $\overline{RAS} = V_{IL}$.
3. Measured with one sequential address change per fast page mode cycle, t_{PC} .
4. $V_{IH} \geq V_{CC} - 0.2 \text{ V}$, $0 \text{ V} \leq V_{IL} \leq 0.2 \text{ V}$.

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DC Characteristics (HM5165400 Series)

		HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Test conditions
Operating current ^{*1, *2}	I _{CC1}	—	130	—	110	mA	t _{RC} = min
Standby current	I _{CC2}	—	2	—	2	mA	TTL interface RAS, CAS = V _{IH} Dout = High-Z
		—	0.5	—	0.5	mA	CMOS interface RAS, CAS ≥ V _{CC} − 0.2 V Dout = High-Z
Standby current (L-version)	I _{CC2}	—	150	—	150	μA	CMOS interface RAS, CAS ≥ V _{CC} − 0.2 V Dout = High-Z
RAS-only refresh current ^{*2}	I _{CC3}	—	130	—	110	mA	t _{RC} = min
Standby current ^{*1}	I _{CC5}	—	5	—	5	mA	RAS = V _{IH} , CAS = V _{IL} Dout = enable
CAS-before-RAS refresh current	I _{CC6}	—	130	—	110	mA	t _{RC} = min
Fast page mode current ^{*1, *3}	I _{CC7}	—	90	—	80	mA	RAS = V _{IL} , CAS cycle, t _{PC} = t _{PC} min
Battery backup current ^{*4} (Standby with CBR refresh) (L-version)	I _{CC10}	—	500	—	500	μA	CMOS interface Dout = High-Z CBR refresh: t _{RC} = 31.3 μs t _{RAS} ≤ 0.3 μs
Self refresh mode current (L-version)	I _{CC11}	—	400	—	400	μA	CMOS interface RAS, CAS ≤ 0.2 V Dout = High-Z
Input leakage current	I _{LI}	−5	5	−5	5	μA	0 V ≤ Vin ≤ V _{CC} + 0.3 V
Output leakage current	I _{LO}	−5	5	−5	5	μA	0 V ≤ Vout ≤ V _{CC} Dout = disable
Output high voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = −2 mA
Output low voltage	V _{OL}	0	0.4	0	0.4	V	Low Iout = 2 mA

- Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.
2. Address can be changed once or less while $\overline{RAS} = V_{IL}$.
3. Measured with one sequential address change per fast page mode cycle, t_{PC} .
4. $V_{IH} \geq V_{CC} - 0.2 \text{ V}$, $0 \text{ V} \leq V_{IL} \leq 0.2 \text{ V}$.

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Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{i1}	—	5	pF	1
Input capacitance (Clocks)	C_{i2}	—	7	pF	1
Output capacitance (Data-in, Data-out)	$C_{i/o}$	—	7	pF	1, 2

Notes : 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. $\overline{\text{RAS}}, \overline{\text{CAS}} = V_{IH}$ to disable Dout.

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AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{ V}$) *¹, *², *¹⁹

Test Conditions

- Input rise and fall time: 5 ns
- Input timing reference levels: 0.8 V, 2.0 V
- Output timing reference levels: 0.8 V, 2.0 V
- Output load: 1 TTL gate + C_L (100 pF) (Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Random read or write cycle time	t _{RC}	90	—	110	—	ns	
$\overline{\text{RAS}}$ precharge time	t _{RP}	30	—	40	—	ns	
$\overline{\text{CAS}}$ precharge time	t _{CP}	8	—	10	—	ns	
$\overline{\text{RAS}}$ pulse width	t _{RAS}	50	10000	60	10000	ns	
$\overline{\text{CAS}}$ pulse width	t _{CAS}	13	10000	15	10000	ns	
Row address setup time	t _{ASR}	0	—	0	—	ns	
Row address hold time	t _{RAH}	8	—	10	—	ns	
Column address setup time	t _{ASC}	0	—	0	—	ns	
Column address hold time	t _{CAH}	8	—	10	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ delay time	t _{RCD}	18	37	20	45	ns	3
$\overline{\text{RAS}}$ to column address delay time	t _{RAD}	13	25	15	30	ns	4
$\overline{\text{RAS}}$ hold time	t _{RSH}	13	—	15	—	ns	
$\overline{\text{CAS}}$ hold time	t _{CSH}	50	—	60	—	ns	
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ precharge time	t _{CRP}	5	—	5	—	ns	
$\overline{\text{OE}}$ to Din delay time	t _{OED}	13	—	15	—	ns	5
$\overline{\text{OE}}$ delay time from Din	t _{DZO}	0	—	0	—	ns	6
$\overline{\text{CAS}}$ delay time from Din	t _{DZC}	0	—	0	—	ns	6
Transition time (rise and fall)	t _T	3	50	3	50	ns	7

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Read Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	50	—	60	ns	8, 9
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	13	—	15	ns	9, 10, 17
Access time from address	t_{AA}	—	25	—	30	ns	9, 11, 17
Access time from $\overline{\text{OE}}$	t_{OEA}	—	13	—	15	ns	9
Read command setup time	t_{RCS}	0	—	0	—	ns	
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	—	0	—	ns	12
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	ns	12
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	25	—	30	—	ns	
Column address to $\overline{\text{CAS}}$ lead time	t_{CAL}	25	—	30	—	ns	
$\overline{\text{CAS}}$ to output in low-Z	t_{CLZ}	0	—	0	—	ns	
Output data hold time	t_{OH}	3	—	3	—	ns	
Output data hold time from $\overline{\text{OE}}$	t_{OHO}	3	—	3	—	ns	
Output buffer turn-off time	t_{OFF}	—	13	—	15	ns	13
Output buffer turn-off to $\overline{\text{OE}}$	t_{OEZ}	—	13	—	15	ns	13
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	13	—	15	—	ns	5

Write Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write command setup time	t _{WCS}	0	—	0	—	ns	14
Write command hold time	t _{WCH}	8	—	10	—	ns	
Write command pulse width	t _{WP}	8	—	10	—	ns	
Write command to RAS lead time	t _{RWL}	13	—	15	—	ns	
Write command to CAS lead time	t _{CWL}	13	—	15	—	ns	
Data-in setup time	t _{DS}	0	—	0	—	ns	15
Data-in hold time	t _{DH}	8	—	10	—	ns	15

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Read-Modify-Write Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read-modify-write cycle time	t _{RWC}	131	—	155	—	ns	
RAS to WE delay time	t _{RWD}	73	—	85	—	ns	14
CAS to WE delay time	t _{CWD}	36	—	40	—	ns	14
Column address to WE delay time	t _{AWD}	48	—	55	—	ns	14
OE hold time from WE	t _{OEH}	13	—	15	—	ns	

Refresh Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
$\overline{CAS}$ setup time (CBR refresh cycle)	t_{CSR}	5	—	5	—	ns	
$\overline{CAS}$ hold time (CBR refresh cycle)	t_{CHR}	8	—	10	—	ns	
$\overline{WE}$ setup time (CBR refresh cycle)	t_{WRP}	0	—	0	—	ns	
$\overline{WE}$ hold time (CBR refresh cycle)	t_{WRH}	8	—	10	—	ns	
$\overline{RAS}$ precharge to $\overline{CAS}$ hold time	t_{RPC}	5	—	5	—	ns	

Fast Page Mode Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Fast page mode cycle time	t _{PC}	35	—	40	—	ns	
Fast page mode $\overline{RAS}$ pulse width	t _{RASP}	—	100000	—	100000	ns	16
Access time from $\overline{CAS}$ precharge	t _{CPA}	—	30	—	35	ns	9, 17
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	t _{CPRH}	30	—	35	—	ns	

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Fast Page Mode Read-Modify-Write Cycle

		HM5164400/HM5165400					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Fast page mode read-modify-write cycle time	t _{PRWC}	76	—	85	—	ns	
$\overline{\text{WE}}$ delay time from $\overline{\text{CAS}}$ precharge	t _{CPW}	53	—	60	—	ns	14

Refresh (HM5164400 Series)

Parameter	Symbol	Max	Unit	Note
Refresh period	t_{REF}	64	ms	8192 cycles
Refresh period (L-version)	t_{REF}	128	ms	8192 cycles

Refresh (HM5165400 Series)

Parameter	Symbol	Max	Unit	Note
Refresh period	t_{REF}	64	ms	4096 cycles
Refresh period (L-version)	t_{REF}	128	ms	4096 cycles

Self Refresh Mode (L-version)

		HM5164400L/HM5165400L					
		-5		-6			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
$\overline{\text{RAS}}$ pulse width (Self refresh)	t_{RASS}	100	—	100	—	μs	23
$\overline{\text{RAS}}$ precharge time (Self refresh)	t_{RPS}	90	—	110	—	ns	23
$\overline{\text{CAS}}$ hold time (Self refresh)	t_{CHS}	−50	—	−50	—	ns	

Notes: 1. AC measurements assume $t_t = 5$ ns.

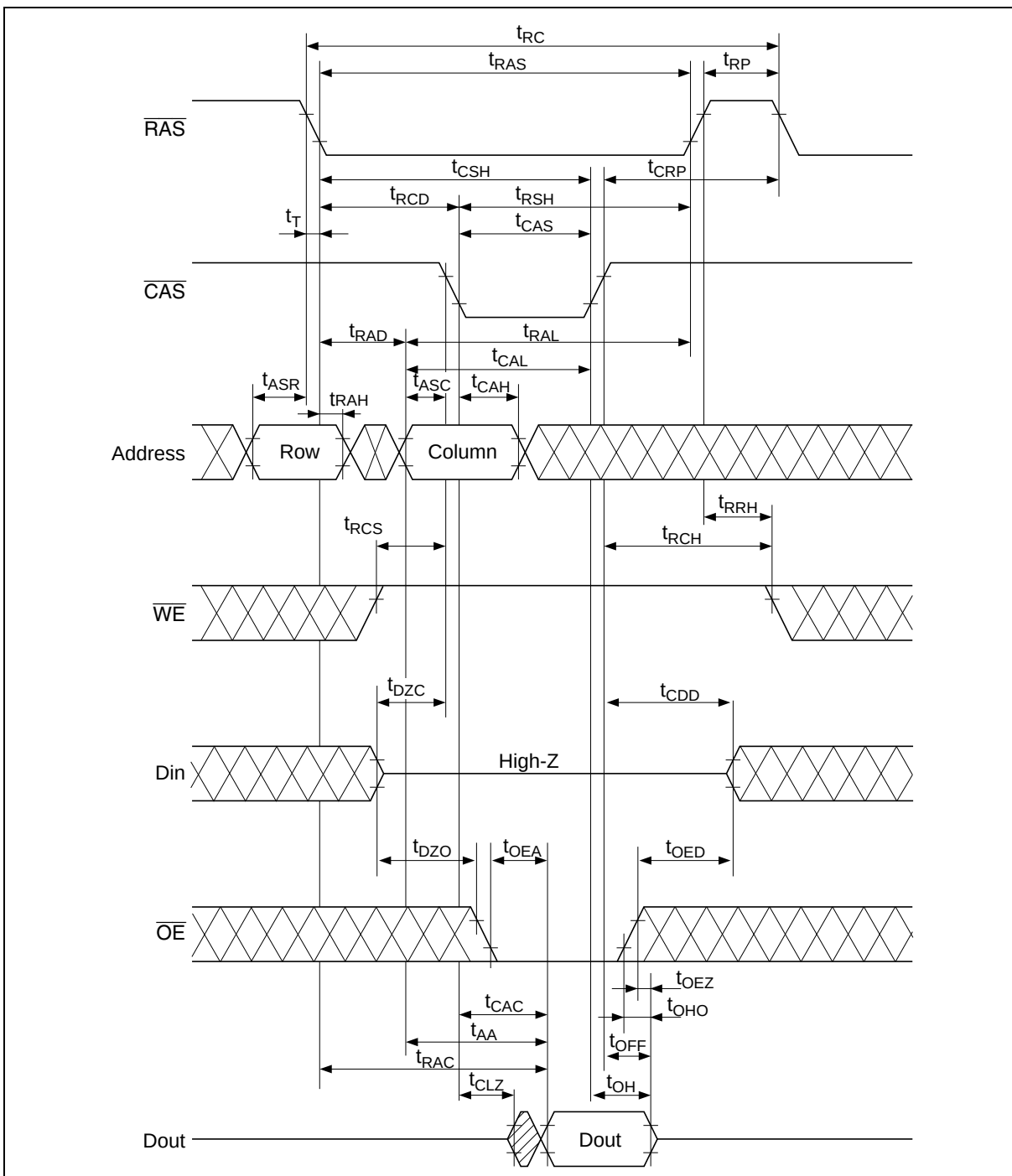
2. An initial pause of 200 μs is required after power up followed by a minimum of eight initialization cycles (any combination of cycles containing $\overline{\text{RAS}}$ -only refresh or $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh).
3. Operation with the t_{RCD} (max) limit insures that t_{RAC} (max) can be met, t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC} .
4. Operation with the t_{RAD} (max) limit insures that t_{RAC} (max) can be met, t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA} .

5. Either t_{OED} or t_{CDD} must be satisfied.
6. Either t_{DZO} or t_{DZC} must be satisfied.
7. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} (min) and V_{IL} (max).
8. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}} (\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}} (\text{max})$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
9. Measured with a load circuit equivalent to 1 TTL loads and 100 pF.
10. Assumes that $t_{\text{RCD}} \geq t_{\text{RCD}} (\text{max})$ and $t_{\text{RCD}} + t_{\text{CAC}} (\text{max}) \geq t_{\text{RAD}} + t_{\text{AA}} (\text{max})$.
11. Assumes that $t_{\text{RAD}} \geq t_{\text{RAD}} (\text{max})$ and $t_{\text{RCD}} + t_{\text{CAC}} (\text{max}) \leq t_{\text{RAD}} + t_{\text{AA}} (\text{max})$.
12. Either t_{RCH} or t_{RRH} must be satisfied for a read cycles.
13. $t_{\text{OFF}} (\text{max})$ and $t_{\text{OEZ}} (\text{max})$ define the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.
14. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPW} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{\text{WCS}} \geq t_{\text{WCS}} (\text{min})$, the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{\text{RWD}} \geq t_{\text{RWD}} (\text{min})$, $t_{\text{CWD}} \geq t_{\text{CWD}} (\text{min})$, and $t_{\text{AWD}} \geq t_{\text{AWD}} (\text{min})$, or $t_{\text{CWD}} \geq t_{\text{CWD}} (\text{min})$, $t_{\text{AWD}} \geq t_{\text{AWD}} (\text{min})$ and $t_{\text{CPW}} \geq t_{\text{CPW}} (\text{min})$, the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
15. t_{DS} , t_{DH} are referred to $\overline{\text{CAS}}$ leading edge in early write cycles and to $\overline{\text{WE}}$ leading edge in delayed write or read-modify-write cycles.
16. t_{RASP} defines $\overline{\text{RAS}}$ pulse width in fast page mode cycles.
17. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{CPA} .
18. In delayed write or read-modify-write cycles, $\overline{\text{OE}}$ must disable output buffer prior to applying data to the device.
19. When output buffers are enabled once, sustain the low impedance state until valid data is obtained. When output buffer is turned on and off within a very short time, generally it causes large $V_{\text{CC}}/V_{\text{SS}}$ line noise, which causes to degrade $V_{\text{IH}} \text{ min}/V_{\text{IL}} \text{ max}$ level.
20. Before and after self refresh mode, execute CBR refresh to all refresh addresses in or within 64 ms period on the condition a and b below.
 - a. Enter self refresh mode within 15.6 μs after either burst refresh or distributed refresh at equal interval to all refresh addresses are completed.
 - b. Start burst refresh or distributed refresh at equal interval to all refresh addresses within 15.6 μs after exiting from self refresh mode.
21. In case of entering from $\overline{\text{RAS}}$ -only-refresh, it is necessary to execute CBR refresh before and after self refresh mode according as note 20.
22. For L-version, it is available to apply each 128 ms and 31.2 μs instead of 64 ms and 15.6 μs at note 20.
23. At $t_{\text{RASS}} > 100 \mu\text{s}$, self refresh mode is activated, and not activated at $t_{\text{RASS}} < 10 \mu\text{s}$. It is undefined within the range of $10 \mu\text{s} \leq t_{\text{RASS}} \leq 100 \mu\text{s}$. For $t_{\text{RASS}} \geq 10 \mu\text{s}$, it is necessary to satisfy t_{RPS} .
24. XXX: H or L (H: $V_{\text{IH}} (\text{min}) \leq V_{\text{IN}} \leq V_{\text{IH}} (\text{max})$, L: $V_{\text{IL}} (\text{min}) \leq V_{\text{IN}} \leq V_{\text{IL}} (\text{max})$)
 //: Invalid Dout
 When the address, clock and input pins are not described on timing waveforms, their pins must be applied V_{IH} or V_{IL} .

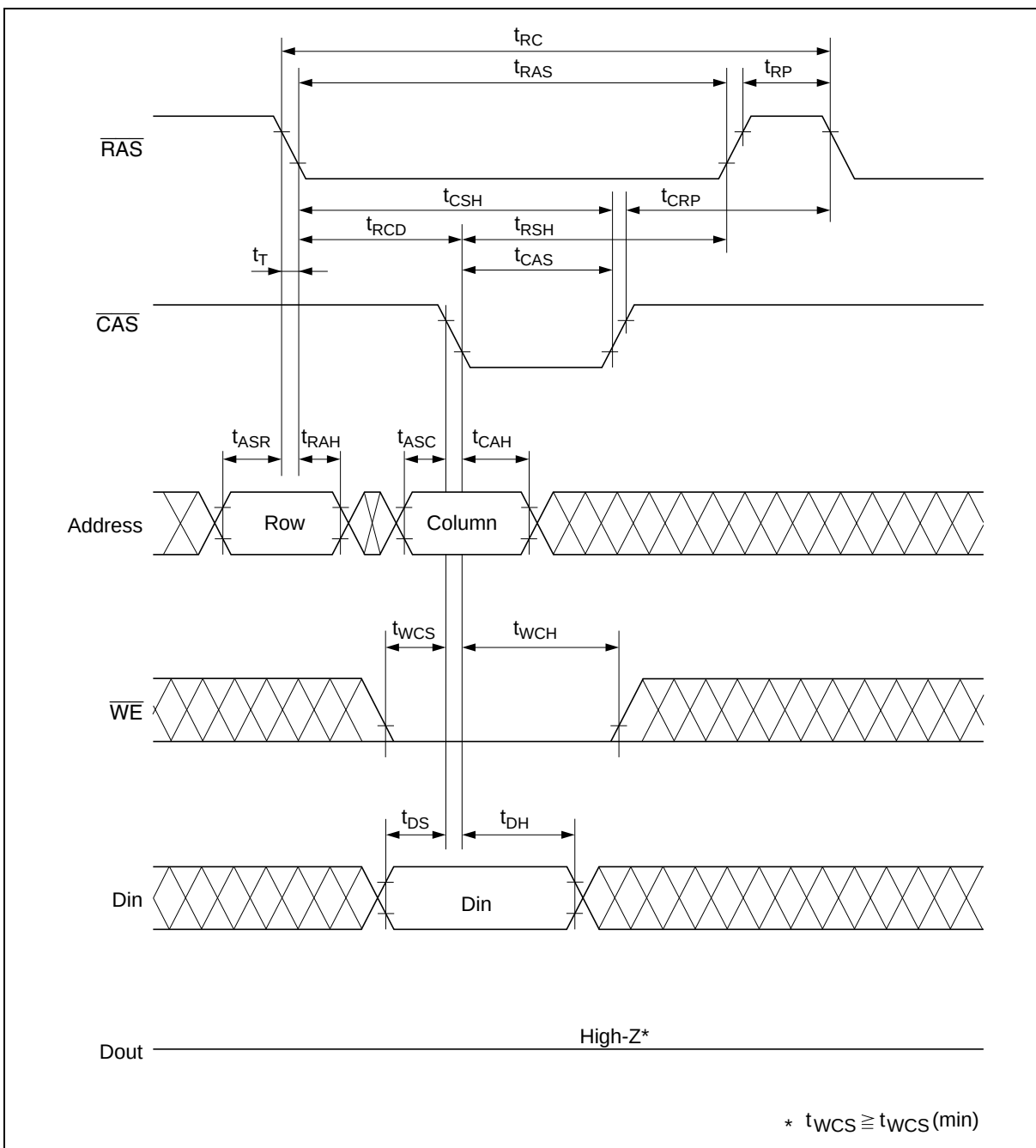
HM5164400 Series, HM5165400 Series

Timing Waveforms*²⁴

Read Cycle

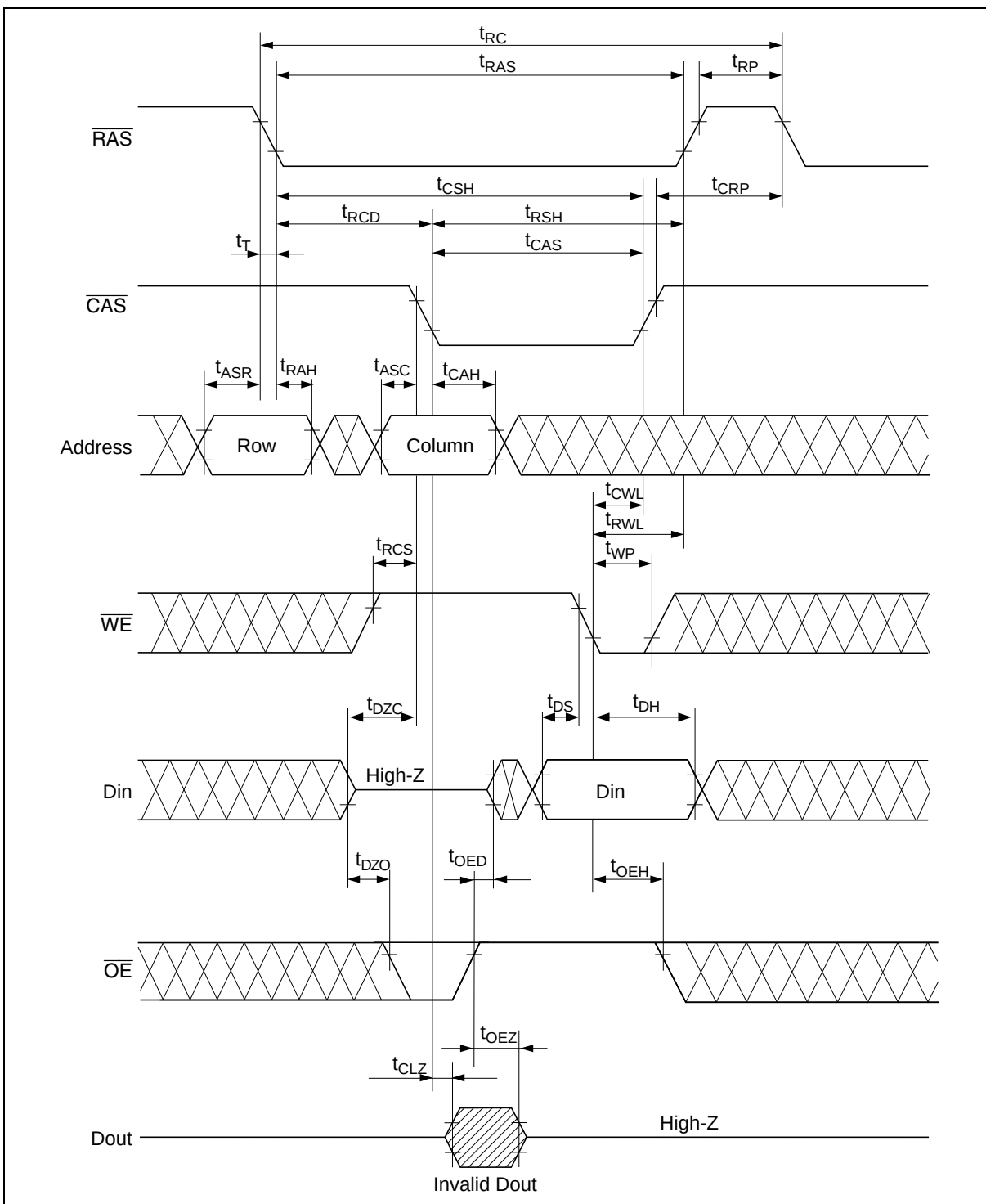


Early Write Cycle

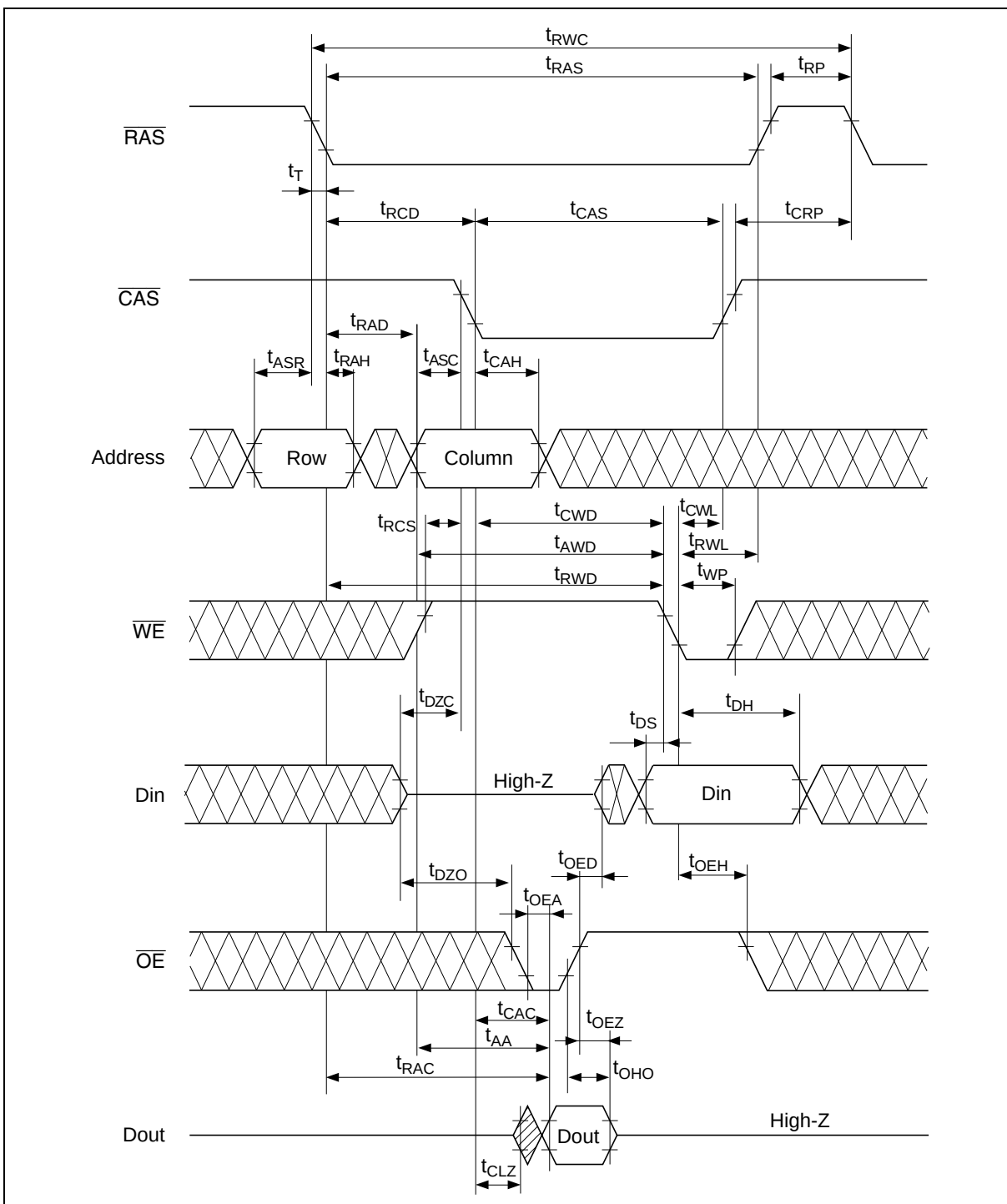


HM5164400 Series, HM5165400 Series

Delayed Write Cycle*¹⁸

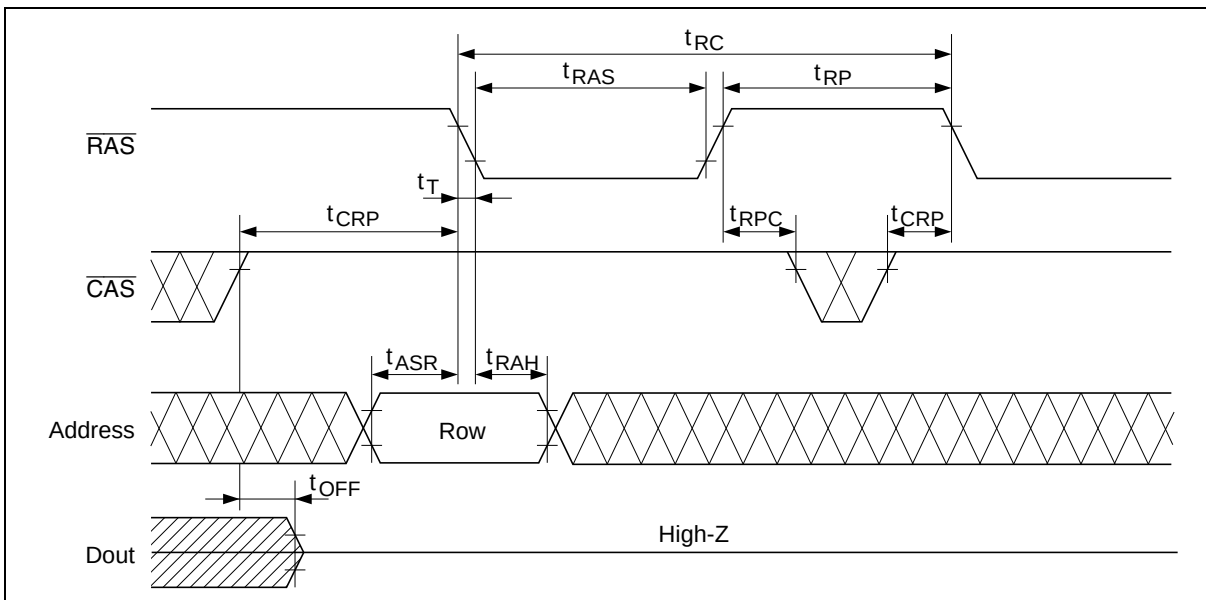


Read-Modify-Write Cycle*¹⁸

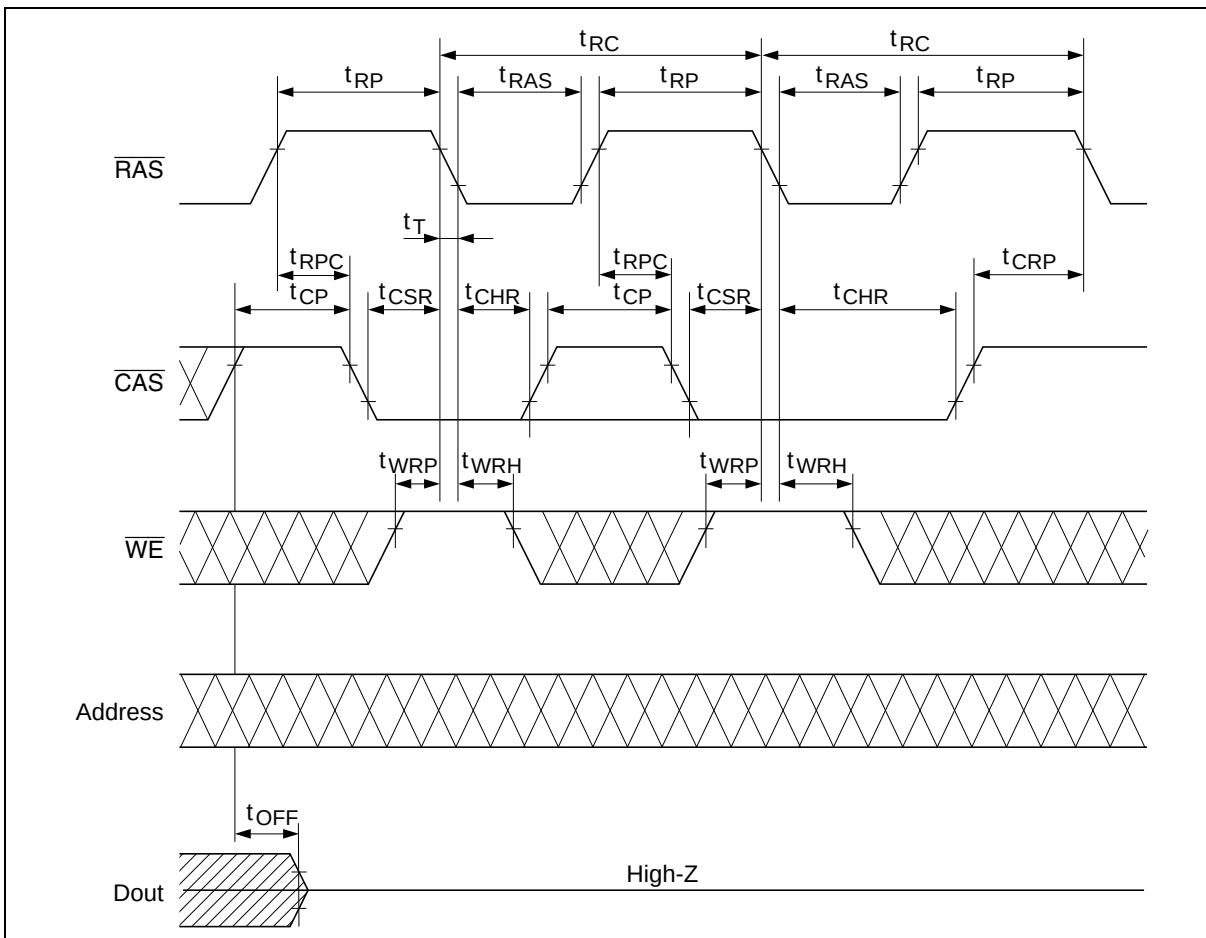


HM5164400 Series, HM5165400 Series

$\overline{\text{RAS}}$ -Only Refresh Cycle

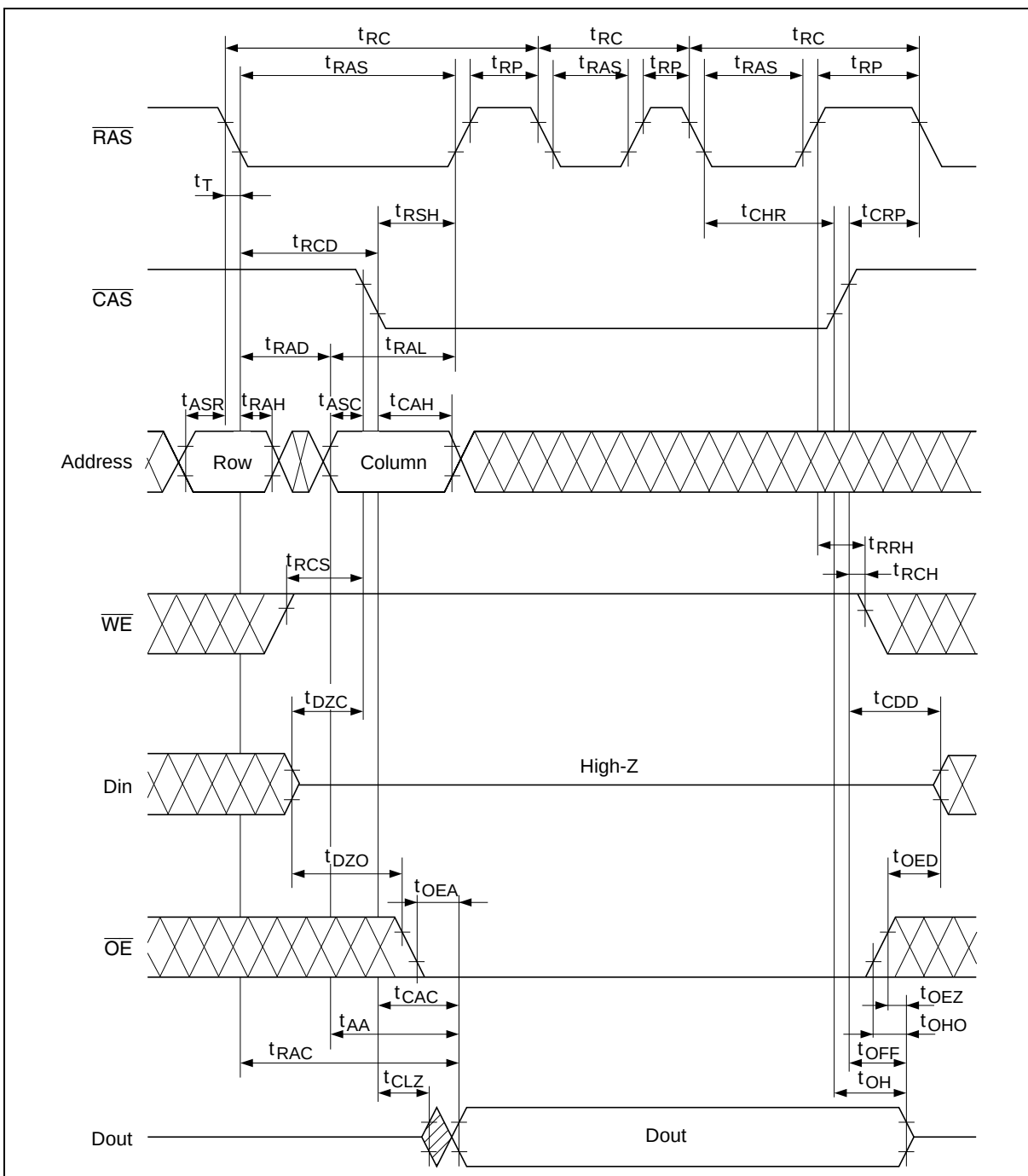


$\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh Cycle

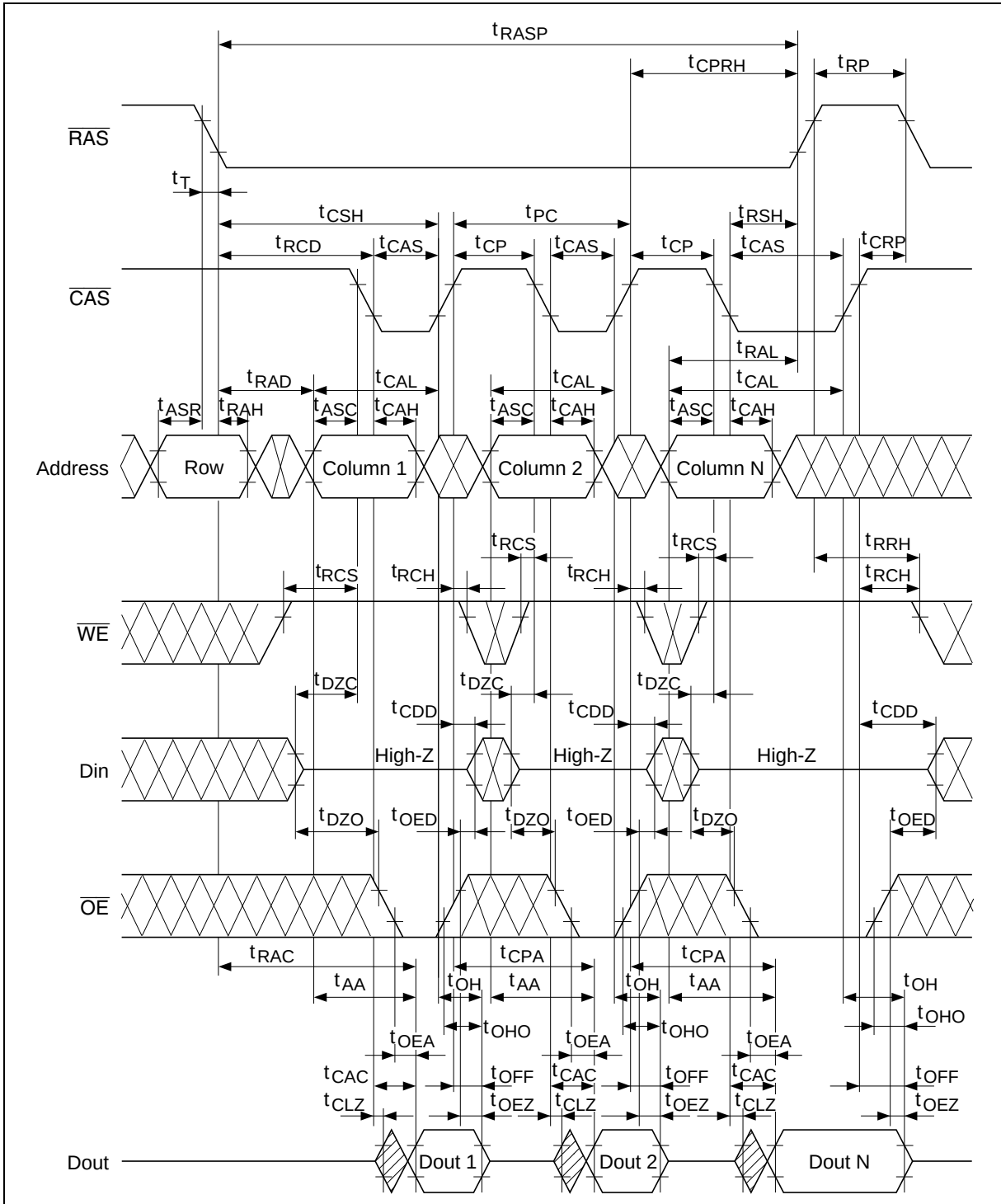


HM5164400 Series, HM5165400 Series

Hidden Refresh Cycle

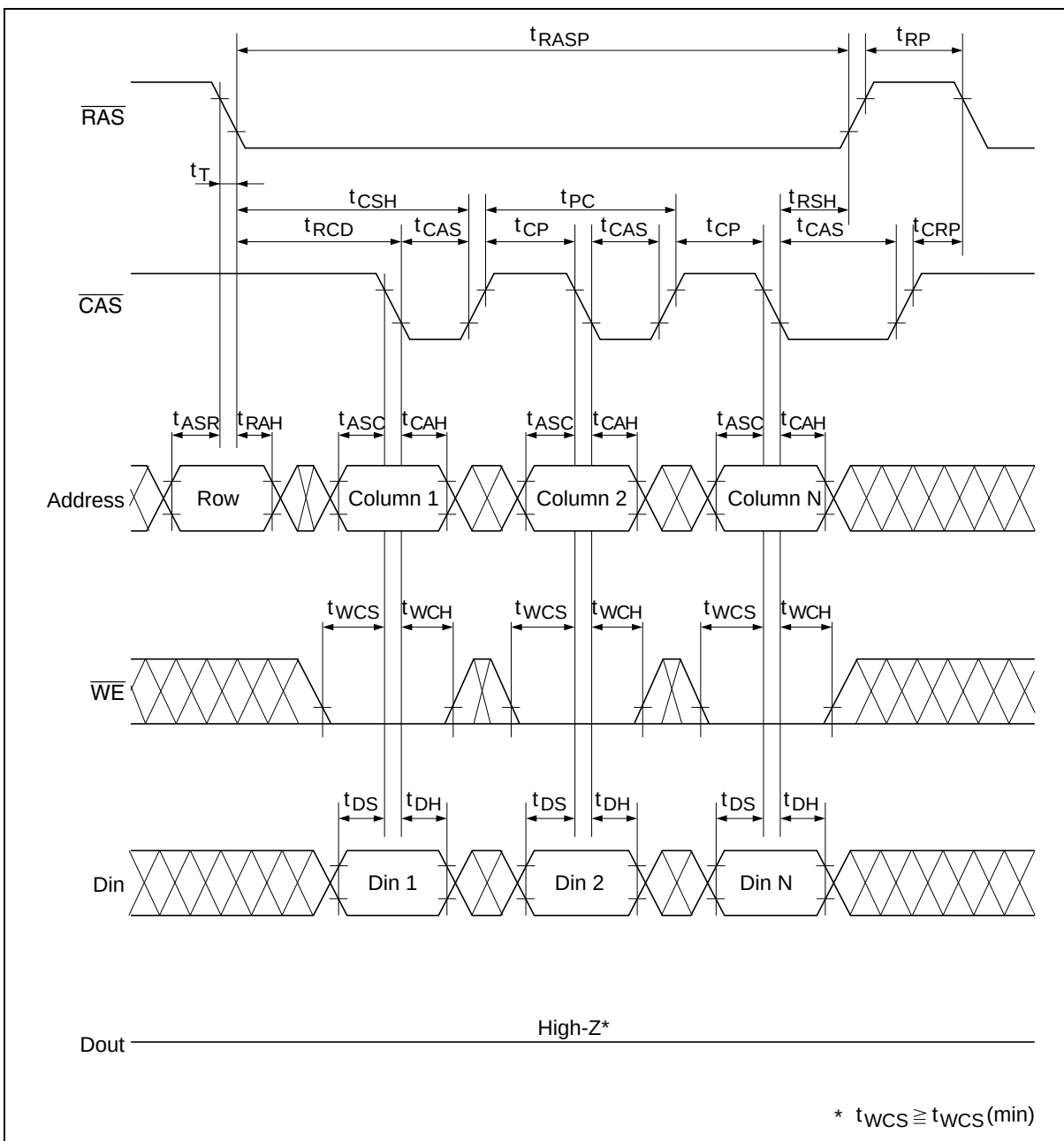


Fast Page Mode Read Cycle

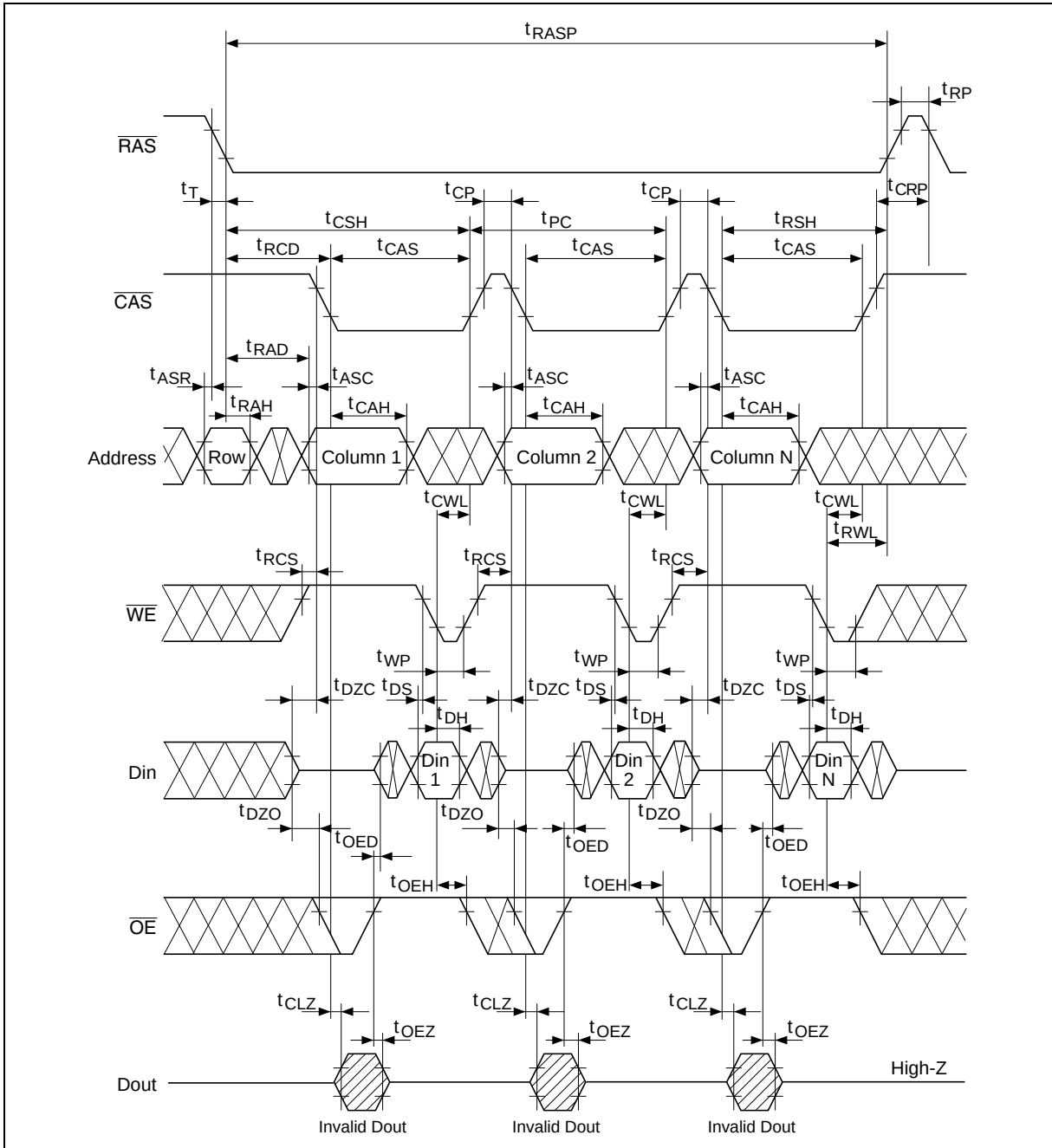


HM5164400 Series, HM5165400 Series

Fast Page Mode Early Write Cycle



Fast Page Mode Delayed Write Cycle*¹⁸

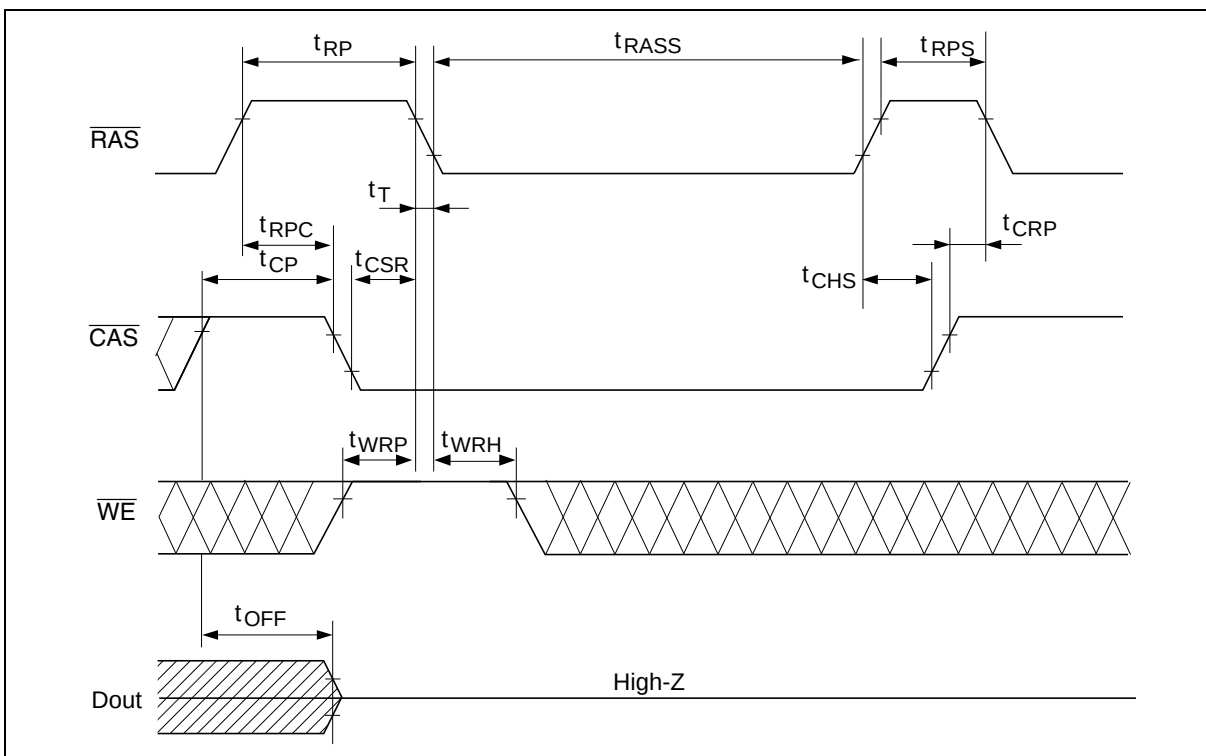


Fast Page Mode Read-Modify-Write Cycle*¹⁸



HM5164400 Series, HM5165400 Series

Self Refresh Cycle (L-version)*^{20, 21, 22, 23}

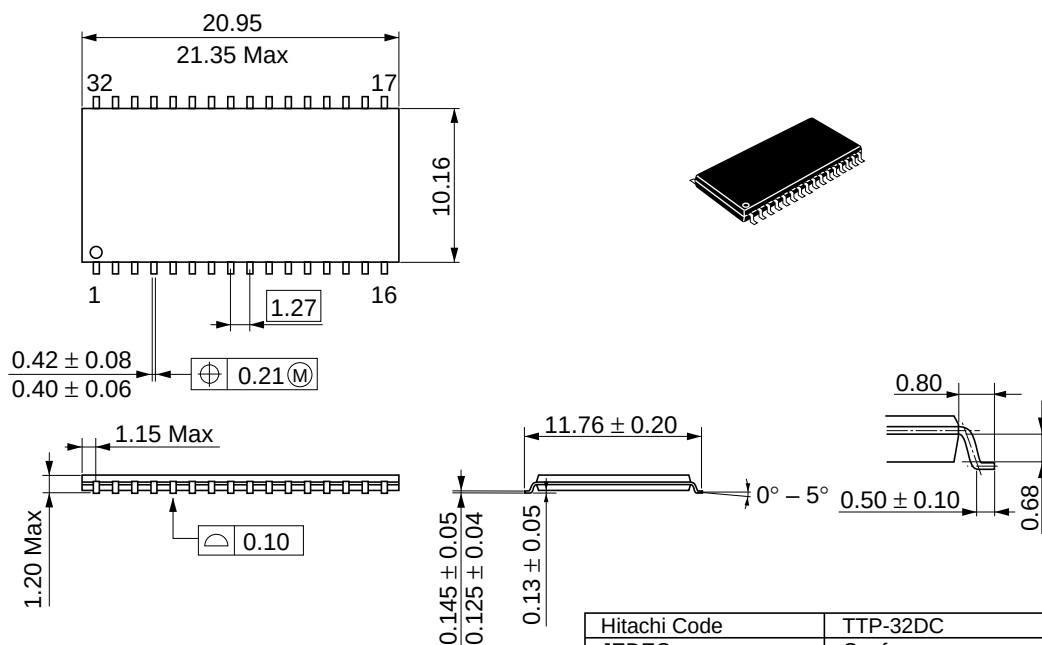


HM5164400 Series, HM5165400 Series

HM5164400TT/LTT Series

HM5165400TT/LTT Series (TTP-32DC)

Unit: mm



Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-32DC
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.51 g

HM5164400 Series, HM5165400 Series

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HM5164400 Series, HM5165400 Series

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Jul. 23, 1997	Initial issue	J. Miyake	M. Saeki
0.1	Nov. 1997	Change of Subtitle	J. Miyake	Y. Takahashi
1.0	Feb. 27, 1998	Deletion of Preliminary		